Zbig R Wasilewski

List of Publications by Year
in descending order

258	9,541	38660 50	45213 90
papers	citations	h-index	g-index

259	259	259	5512
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Coupling and Entangling of Quantum States in Quantum Dot Molecules. Science, 2001, 291, 451-453.	6.0	759
2	Terahertz quantum cascade lasers operating up to â^¼ 200 K with optimized oscillator strength and improved injection tunneling. Optics Express, 2012, 20, 3866.	1.7	493
3	Addition spectrum of a lateral dot from Coulomb and spin-blockade spectroscopy. Physical Review B, 2000, 61, R16315-R16318.	1.1	369
4	Phase-Controlled Currents in Semiconductors. Physical Review Letters, 1995, 74, 3596-3599.	2.9	338
5	Quantum dot infrared photodetectors. Applied Physics Letters, 2001, 78, 79-81.	1.5	293
6	Negative capacitance effect in semiconductor devices. IEEE Transactions on Electron Devices, 1998, 45, 2196-2206.	1.6	268
7	High-power portable terahertz laser systems. Nature Photonics, 2021, 15, 16-20.	15.6	228
8	Coherent control of three-spin states in a triple quantum dot. Nature Physics, 2012, 8, 54-58.	6.5	215
9	InAs selfâ€assembled quantum dots on InP by molecular beam epitaxy. Applied Physics Letters, 1996, 68, 991-993.	1.5	183
10	Manipulating the energy levels of semiconductor quantum dots. Physical Review B, 1999, 59, 15368-15373.	1.1	169
11	Mode-locked pulses from mid-infrared Quantum Cascade Lasers. Optics Express, 2009, 17, 12929.	1.7	168
12	Fractal Conductance Fluctuations in a Soft-Wall Stadium and a Sinai Billiard. Physical Review Letters, 1998, 80, 1948-1951.	2.9	153
13	Terahertz quantum-cascade lasers based on a three-well active module. Applied Physics Letters, 2007, 90, 041112.	1.5	151
14	Background-limited terahertz quantum-well photodetector. Applied Physics Letters, 2005, 86, 231103.	1.5	121
15	Excitonic Energy Shell Structure of Self-Assembled InGaAs/GaAs Quantum Dots. Physical Review Letters, 2004, 92, 187402.	2.9	111
16	How good is the polarization selection rule for intersubband transitions?. Applied Physics Letters, 1998, 72, 1682-1684.	1.5	110
17	Segregation of Si Î´ doping in GaAsâ€AlGaAs quantum wells and the cause of the asymmetry in the currentâ€voltage characteristics of intersubband infrared detectors. Applied Physics Letters, 1993, 63, 761-763.	1.5	100
18	Exciton Dephasing in Quantum Dot Molecules. Physical Review Letters, 2003, 91, 267401.	2.9	100

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19	Integrated quantum well intersub-band photodetector and light emitting diode. Electronics Letters, 1995, 31, 832-833.	0.5	97
20	Self-Similar Magnetoresistance of a Semiconductor Sinai Billiard. Physical Review Letters, 1997, 78, 1952-1955.	2.9	97
21	High-frequency quantum-well infrared photodetectors measured by microwave-rectification technique. IEEE Journal of Quantum Electronics, 1996, 32, 1024-1028.	1.0	95
22	Composition of AlGaAs. Journal of Applied Physics, 1997, 81, 1683-1694.	1.1	95
23	Microwave radiation induced magneto-oscillations in the longitudinal and transverse resistance of a two-dimensional electron gas. Solid State Communications, 2004, 129, 341-345.	0.9	89
24	Bipolar spin blockade and coherent state superpositions in a triple quantum dot. Nature Nanotechnology, 2013, 8, 261-265.	15.6	83
25	Coupled Electron-Phonon Modes in Optically Pumped Resonant Intersubband Lasers. Physical Review Letters, 2003, 90, 077402.	2.9	81
26	Frequency quenching of microwave-induced resistance oscillations in a high-mobility two-dimensional electron gas. Physical Review B, 2007, 76, .	1.1	79
27	Multicolor voltage-tunable quantum-well infrared photodetector. IEEE Electron Device Letters, 1993, 14, 566-568.	2.2	77
28	Unusual capacitance behavior of quantum well infrared photodetectors. Applied Physics Letters, 1997, 70, 1828-1830.	1.5	77
29	Coupled InAs/GaAs quantum dots with well-defined electronic shells. Applied Physics Letters, 2000, 76, 2268-2270.	1.5	75
30	Resistively Detected Nuclear Magnetic Resonance in the Quantum Hall Regime: Possible Evidence for a Skyrme Crystal. Physical Review Letters, 2002, 88, 256807.	2.9	75
31	Effect of doping concentration on the performance of terahertz quantum-cascade lasers. Applied Physics Letters, 2005, 87, 141102.	1.5	75
32	Three-dimensional transport diagram of a triple quantum dot. Physical Review B, 2010, 82, .	1.1	74
33	Dark current in quantum well infrared photodetectors. Journal of Applied Physics, 1993, 73, 2029-2031.	1.1	73
34	Photoconductivity nonlinearity at high excitation power in quantum well infrared photodetectors. Applied Physics Letters, 1997, 70, 414-416.	1.5	67
35	High absorption (>90%) quantum-well infrared photodetectors. Applied Physics Letters, 2001, 79, 4237-4239.	1.5	66
36	Blue-violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 011114.	1.5	66

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37	Magneto-optical studies of n-GaAs under high hydrostatic pressure. Semiconductor Science and Technology, 1986, 1, 264-274.	1.0	63
38	Enhanced degradation resistance of quantum dot lasers to radiation damage. Applied Physics Letters, 2000, 77, 624-626.	1.5	61
39	Band-gap energy ofInxGa1â^'xNyAs1â^'yas a function of N content. Physical Review B, 2002, 66, .	1.1	59
40	From laterally modulated two-dimensional electron gas towards artificial graphene. New Journal of Physics, 2012, 14, 053002.	1.2	59
41	Lasing in quantum-dot ensembles with sharp adjustable electronic shells. Applied Physics Letters, 1999, 75, 986-988.	1.5	58
42	A phonon scattering assisted injection and extraction based terahertz quantum cascade laser. Journal of Applied Physics, 2012, 111, .	1.1	58
43	Pixelless infrared imaging device. Electronics Letters, 1997, 33, 379.	0.5	57
44	High mobility two-dimensional electron gas in AlGaNâ•GaN heterostructures grown on bulk GaN by plasma assisted molecular beam epitaxy. Applied Physics Letters, 2005, 86, 102106.	1.5	56
45	Nitride-based laser diodes grown by plasma-assisted molecular beam epitaxy. Journal Physics D: Applied Physics, 2014, 47, 073001.	1.3	56
46	Collapse of the Zeeman gap in quantum dots due to electronic correlations. Physical Review B, 1999, 59, 2801-2806.	1.1	54
47	GaAs/AlGaAs quantum-well photodetector for visible and middle infrared dual-band detection. Applied Physics Letters, 2000, 77, 2437-2439.	1.5	54
48	Importance of the upper state position in the performance of quantum well intersubband infrared detectors. Applied Physics Letters, 1991, 59, 3625-3627.	1.5	53
49	Attenuation and velocity of 56 GHz longitudinal phonons in gallium arsenide from 50 to 300 K. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1994, 70, 687-698.	0.6	53
50	Shot-noise suppression in resonant tunneling. Physical Review B, 1995, 51, 5116-5120.	1.1	51
51	Studies of oxide desorption from GaAs substrates via Ga[sub 2]O[sub 3] to Ga[sub 2]O conversion by exposure to Ga flux. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 1534.	1.6	51
52	Intersubband Raman Laser. Applied Physics Letters, 2001, 78, 3580-3582.	1.5	50
53	Quantum interference and phonon-mediated back-action in lateral quantum-dot circuits. Nature Physics, 2012, 8, 522-527.	6.5	50
54	Determination of the size, shape, and composition of indium-flushed self-assembled quantum dots by transmission electron microscopy. Journal of Applied Physics, 2000, 88, 2272-2277.	1.1	49

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55	Optimized GaAsâˆ•AlGaAs light-emitting diodes and high efficiency wafer-fused optical up-conversion devices. Journal of Applied Physics, 2004, 96, 5243-5248.	1.1	48
56	Pixelless thermal imaging with integrated quantum-well infrared photodetector and light-emitting diode. IEEE Photonics Technology Letters, 2002, 14, 182-184.	1.3	47
57	Uncooled infrared detectors for 3â€“5Î¼m and beyond. Applied Physics Letters, 2008, 93, .	1.5	47
58	Tunnel current in quantum dot infrared photodetectors. Journal of Applied Physics, 2003, 93, 1320-1322.	1.1	46
59	AlGaAs emitterâˆ•GaAs barrier terahertz detector with a 2.3 THz threshold. Applied Physics Letters, 2005, 86, 071112.	1.5	46
60	Nonequivalent atomic step edgesâ€”Role of gallium and nitrogen atoms in the growth of InGaN layers. Journal of Crystal Growth, 2013, 367, 115-121.	0.7	46
61	Self-assembled quantum dots: five years later. Superlattices and Microstructures, 1999, 25, 87-96.	1.4	45
62	Nitride-based laser diodes by plasma-assisted MBEâ€”From violet to green emission. Journal of Crystal Growth, 2009, 311, 1632-1639.	0.7	45
63	Pixelless infrared imaging utilizing a p-type quantum well infrared photodetector integrated with a light emitting diode. Applied Physics Letters, 1997, 70, 2784-2786.	1.5	43
64	Light-hole and heavy-hole transitions for high-temperature long-wavelength infrared detection. Applied Physics Letters, 2010, 97, .	1.5	43
65	Quantum oscillations in the microwave magnetoabsorption of a two-dimensional electron gas. Physical Review B, 2010, 81, .	1.1	43
66	InAs/GaAs(100) self-assembled quantum dots: arsenic pressure and capping effects. Journal of Crystal Growth, 2002, 236, 145-154.	0.7	42
67	Studies and modeling of growth uniformity in molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1991, 9, 120.	1.6	41
68	Influence of the number of wells in the performance of multiple quantum well intersubband infrared detectors. Journal of Applied Physics, 1992, 72, 1062-1064.	1.1	40
69	Optical phonons inAlxGa1âˆ’xAs: Raman spectroscopy. Physical Review B, 2004, 70, .	1.1	40
70	Emission from a highly excited singleInAsâˆ’GaAsquantum dot in magnetic fields: An excitonic Fock-Darwin diagram. Physical Review B, 2006, 74, .	1.1	40
71	Enhanced charge detection of spin qubit readout via an intermediate state. Applied Physics Letters, 2012, 101, .	1.5	40
72	Heterojunction wavelength-tailorable far-infrared photodetectors with response out to 70 Î¼m. Applied Physics Letters, 2001, 78, 2241-2243.	1.5	39

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73	Cutoff tailorability of heterojunction terahertz detectors. Applied Physics Letters, 2003, 82, 139-141.	1.5	39
74	Intersubband transitions in InGaNAs/GaAs quantum wells. Applied Physics Letters, 2002, 81, 1836-1838.	1.5	38
75	Effect of oscillator strength and intermediate resonance on the performance of resonant phonon-based terahertz quantum cascade lasers. Journal of Applied Physics, 2013, 113, 113109.	1.1	38
76	Few-Electron Open Dots: Single Level Transport. Physical Review Letters, 1999, 83, 1838-1841.	2.9	37
77	Quantum Hall ferromagnet at high filling factors: A magnetic-field-induced Stoner transition. Physical Review B, 2005, 72, .	1.1	37
78	Growth optimisation of the GaN layers and GaN/AlGaN heterojunctions on bulk GaN substrates using plasma-assisted molecular beam epitaxy. Physica Status Solidi A, 2004, 201, 320-323.	1.7	36
79	High power blueâ€“violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular beam epitaxy. Semiconductor Science and Technology, 2005, 20, 809-813.	1.0	36
80	Terahertz Emission in Asymmetric Quantum Wells by Frequency Mixing of Midinfrared Waves. IEEE Journal of Quantum Electronics, 2006, 42, 1157-1174.	1.0	36
81	Evolution of the energy levels in quantum dot ensembles with different densities. Applied Physics Letters, 1999, 75, 1866-1868.	1.5	35
82	Voltageâ€tuning in multiâ€color quantum well infrared photodetector stacks. Journal of Applied Physics, 1996, 79, 8091-8097.	1.1	33
83	Terahertz Quantum Well Photodetectors. IEEE Journal of Selected Topics in Quantum Electronics, 2008, 14, 374-377.	1.9	33
84	InGaN light emitting diodes for 415 nmâ€“520 nm spectral range by plasma assisted MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S917.	0.8	32
85	Metal-Grating-Coupled Terahertz Quantum-Well Photodetectors. IEEE Electron Device Letters, 2011, 32, 659-661.	2.2	31
86	Long time relaxation phenomena of a two-dimensional electron system within integer quantum Hall plateau regimes after magnetic field sweeps. Physical Review B, 2004, 69, .	1.1	30
87	Two-band electron transport in a double quantum well. Physical Review B, 2005, 71, .	1.1	30
88	Excitonic complexes in natural InAs/GaAs quantum dots. Physical Review B, 2015, 91, .	1.1	30
89	Charge nonâ€neutrality in the quantum well region of a GaAsâ€AlGaAs intersubband 9 Î¼m detector. Applied Physics Letters, 1991, 58, 1059-1061.	1.5	28
90	Phase Diagram for the Breakdown of the Quantum Hall Effect. Physical Review Letters, 1999, 82, 1249-1252.	2.9	28

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91	An indirectly pumped terahertz quantum cascade laser with low injection coupling strength operating above 150â€‰K. Journal of Applied Physics, 2013, 113, .	1.1	28
92	Pixel-less infrared imaging based on the integration of an n-type quantum-well infrared photodetector with a light-emitting diode. Applied Physics Letters, 1999, 75, 563-565.	1.5	27
93	Natural quantum dots in the InAsâ•GaAs wetting layer. Applied Physics Letters, 2008, 92, 171104.	1.5	27
94	Midinfrared optical upconverter. Applied Physics Letters, 2005, 86, 201103.	1.5	26
95	Intersubband photocurrent from the quantum well of an asymmetrical doubleâ€barrier structure. Journal of Applied Physics, 1991, 70, 935-940.	1.1	25
96	Postgrowth tuning of quantumâ€well infrared detectors by rapid thermal annealing. Journal of Applied Physics, 1994, 75, 8234-8236.	1.1	25
97	Noise and photoconductive gain in AlGaAs/GaAs quantum well intersubband infrared photodetectors. Journal of Applied Physics, 1994, 76, 1889-1894.	1.1	25
98	Growth mechanism of InGaN by plasma assisted molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 03C136.	0.6	25
99	The enhancement of quantum well intermixing through repeated ion implantation. Semiconductor Science and Technology, 1994, 9, 2134-2137.	1.0	24
100	Quantum Interference between Three Two-Spin States in a Double Quantum Dot. Physical Review Letters, 2012, 108, 226802.	2.9	24
101	Low dark current dual band infrared photodetector using thin AlAs barriers and Î“â€X mixed intersubband transition in GaAs quantum wells. Applied Physics Letters, 1994, 64, 475-477.	1.5	23
102	Enhanced compositional disordering of quantum wells in GaAs/AlGaAs and InGaAs/GaAs using focused Ga+ion beams. Applied Physics Letters, 1994, 65, 621-623.	1.5	22
103	Intersubband infrared detector with optimized valence band quantum wells for 3â€“5 Î¼m wavelength region. Journal of Applied Physics, 1999, 85, 2972-2976.	1.1	22
104	Inhomogeneous broadening in quantum dots with ternary aluminum alloys. Applied Physics Letters, 2001, 79, 2701-2703.	1.5	22
105	Twoâ€photon intersubband transitions in quantum well infrared photoconductors. Applied Physics Letters, 1994, 65, 1560-1562.	1.5	21
106	Studies of Si segregation in GaAs using currentâ€“voltage characteristics of quantum well infrared photodetectors. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 1273.	1.6	20
107	Quasi-phase matched second-harmonic generation in an AlxGa1â^'xAs asymmetric quantum-well waveguide using ion-implantation-enhanced intermixing. Applied Physics Letters, 2000, 77, 4247-4249.	1.5	20
108	Microwave measurement of shot noise in resonant tunneling diodes. Applied Physics Letters, 1997, 71, 530-532.	1.5	19

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109	Time-Resolved Thermal Quenching of THz Quantum Cascade Lasers. IEEE Journal of Quantum Electronics, 2010, 46, 396-404.	1.0	19
110	A high carrier injection terahertz quantum cascade laser based on indirectly pumped scheme. Applied Physics Letters, 2014, 104, 041111.	1.5	19
111	MBE growth of continuously-graded parabolic quantum well arrays in AlGaAs. Journal of Crystal Growth, 2019, 514, 103-108.	0.7	19
112	Measurements of intersubband photocurrents from quantum wells in asymmetrical-double-barrier structures. Physical Review B, 1991, 44, 1411-1414.	1.1	18
113	1.5 Î¼m to 0.87 Î¼m optical upconversion using wafer fusion technology. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 788.	0.9	18
114	Optical upconverter with integrated heterojunction phototransistor and light-emitting diode. Applied Physics Letters, 2006, 88, 073501.	1.5	18
115	Optimal Doping Density for Quantum-Well Infrared Photodetector Performance. IEEE Journal of Quantum Electronics, 2009, 45, 623-628.	1.0	18
116	Short wavelength (1â€“4 Î¼m) infrared detectors using intersubband transitions in GaAs-based quantum wells. Journal of Applied Physics, 1998, 83, 6178-6181.	1.1	17
117	A study of GaAs/AlGaAs p-type quantum well infrared photodetectors with different barrier heights. Journal of Applied Physics, 1998, 83, 585-587.	1.1	17
118	Transient photocurrent overshoot in quantum-well infrared photodetectors. Applied Physics Letters, 2001, 79, 2094-2096.	1.5	17
119	Fock-Darwin spectrum of a single InAs/GaAs quantum dot. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 3748-3751.	0.8	17
120	Dresselhaus spin-orbit coupling in a symmetric (100) GaAs quantum well. Physical Review B, 2006, 74, .	1.1	17
121	InGaN laser diodes operating at 450â€“460 nm grown by rf-plasma MBE. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 02B102.	0.6	17
122	CdTeâ€Cd1â^'xMnxTe multiple quantum well structures grown by pulsed laser evaporation and epitaxy. Applied Physics Letters, 1991, 59, 1591-1593.	1.5	16
123	Low threshold optical bistable switching in an asymmetric Î»/4â€shifted distributedâ€feedback heterostructure. Applied Physics Letters, 1995, 67, 1051-1053.	1.5	16
124	Mid-wavelength infrared detection with InxGa1-xAs/Al0.45Ga0.55As multiple quantum well structures. Semiconductor Science and Technology, 1995, 10, 45-48.	1.0	15
125	Terahertz quantum well infrared detectors. Infrared Physics and Technology, 2009, 52, 289-293.	1.3	15
126	Realization of Harmonic Oscillator Arrays with Graded Semiconductor Quantum Wells. Physical Review Letters, 2020, 125, 097403.	2.9	15

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127	Transport measurements of resonant-tunneling widths. Physical Review B, 1991, 43, 7086-7090.	1.1	14
128	Regular periodic intersubband photocurrent peaks in a multiple double-well structure. Physical Review B, 1993, 48, 1951-1954.	1.1	14
129	Effect of the shape of the first barrier on quantum well infrared photodetector performance. Journal of Applied Physics, 1997, 82, 889-892.	1.1	14
130	Quasiphase matched surface emitting second harmonic generation in periodically reversed asymmetric GaAs/AlGaAs quantum well waveguide. Applied Physics Letters, 1997, 70, 2655-2657.	1.5	14
131	Terahertz quantum cascade lasers: Fabrication, characterization, and doping effect. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 778-782.	0.9	14
132	Coherent exchange and double beam splitter oscillations in a triple quantum dot. Physical Review B, 2012, 86, .	1.1	14
133	Experimental investigation of terahertz quantum cascade laser with variable barrier heights. Journal of Applied Physics, 2014, 115, 163103.	1.1	14
134	Experimental study of intersubband infrared transitions in coupled quantum wells under an electric field. Journal of Applied Physics, 1990, 68, 3780-3782.	1.1	13
135	Widely tunable self-assembled quantum dot lasers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 578-581.	0.9	13
136	Infrared reflectivity of (GaAs)m/(AlAs)n superlattices. Applied Physics Letters, 2003, 83, 3683-3685.	1.5	13
137	Thermopower of a double quantum well based on GaAs. Physical Review B, 2003, 67, .	1.1	13
138	Role of Sb in the growth and optical properties of 1.55Î¼m GaInN(Sb)Asâ•GaNAs quantum-well structures by molecular-beam epitaxy. Applied Physics Letters, 2005, 87, 181908.	1.5	13
139	High current density tunnel diodes for multi-junction photovoltaic devices on InP substrates. Applied Physics Letters, 2021, 118, .	1.5	13
140	Infrared transmission and photocurrent study of intersubband transitions in a coupled asymmetrical quantum well structure. Journal of Applied Physics, 1991, 70, 7560-7563.	1.1	12
141	Fano resonance mediated by intersubband-phonon coupling. Applied Physics Letters, 2007, 91, 131121.	1.5	12
142	Electrically switching transverse modes in high power THz quantum cascade lasers. Optics Express, 2010, 18, 10036.	1.7	12
143	Dispersive line shape in the vicinity of the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î½</mml:mi><mml:mo>=</mml:mo><mml:mn>1</mml:mn> Hall state: Coexistence of Knight-shifted and unshifted resistively detected NMR responses. Physical Review B, 2013, 88, .	1.1	12
144	Role of metastable charge states in a quantum-dot spin-qubit readout. Physical Review B, 2015, 92, .	1.1	12

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145	Measurement of indium segregation in strained In_xGa_{1â€”x}As/GaAs quantum wells by transmission electron microscopy. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1997, 75, 803-821.	0.8	11
146	Grazing-angle intersubband absorption inn-doped GaAs multiple quantum wells. Physical Review B, 2000, 61, 13050-13054.	1.1	11
147	Influence of the single-particle Zeeman energy on the quantum Hall ferromagnet at high filling factors. Physical Review B, 2007, 75, .	1.1	11
148	Photovoltaic infrared detection with p-type graded barrier heterostructures. Journal of Applied Physics, 2012, 111, .	1.1	11
149	Visibility study of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>S</mml:mi><mml:mtext>â^’</mml:mtext><mml:msub><r oscillations without applied initialization. Physical Review B, 2015, 91, .	1.1	11
150	Thermally activated currentâ€“voltage asymmetry in quantum-well inter-subband photodetectors. Canadian Journal of Physics, 1996, 74, 9-15.	0.4	10
151	An asymmetric quantum well infrared photodetector with voltageâ€tunable narrow and broadâ€band response. Journal of Applied Physics, 1996, 79, 3307-3311.	1.1	10
152	QWIPs DESIGNED FOR HIGH ABSORPTION AND HIGH OPERATING TEMPERATURE. International Journal of High Speed Electronics and Systems, 2002, 12, 803-819.	0.3	10
153	Normal incidence detection of ultraviolet, visible, and mid-infrared radiation in a single GaAs/AlGaAs device. Optics Letters, 2009, 34, 2036.	1.7	10
154	Polarization Sensitivity of Quantum Well Infrared Photodetector Coupled to a Metallic Diffraction Grid. IEEE Journal of Quantum Electronics, 2010, 46, 877-883.	1.0	10
155	Effects of interface roughness scattering on device performance of indirectly pumped terahertz quantum cascade lasers. Journal of Physics: Conference Series, 2015, 619, 012003.	0.3	10
156	Single quantum well intersubband infrared detector using GaAs-AlGaAs asymmetrical double-barrier structures. Semiconductor Science and Technology, 1991, 6, C124-C127.	1.0	9
157	Nonuniform vertical charge transport and relaxation in quantum well infrared detectors. Journal of Applied Physics, 1998, 83, 991-997.	1.1	9
158	Optimization of p-doping in GaAs photon-recycling light-emitting diodes operated at low temperature. Semiconductor Science and Technology, 2001, 16, L21-L23.	1.0	9
159	Observation of resonant tunneling through a self-assembled InAs quantum dot layer. Applied Physics Letters, 2006, 88, 043103.	1.5	9
160	Improved thickness uniformity in molecular beam epitaxial growth of GaAs using a tilted conical insert crucible. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1991, 9, 3175-3177.	0.9	8
161	Temperature dependence of photoresponse inp-typeGaAs/AlxGa1â^’xAsmultiple quantum wells:â€ƒTheory and experiment. Physical Review B, 2000, 61, 13798-13804.	1.1	8
162	Decay of long-lived quantum Hall induced currents in 2D electron systems. New Journal of Physics, 2007, 9, 71-71.	1.2	8

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163	Analysis of Dark Current Mechanisms for Split-Off Band Infrared Detectors at High Temperatures. IEEE Transactions on Electron Devices, 2010, 57, 1230-1236.	1.6	8
164	Nonlinear magnetotransport phenomena in high-mobility two-dimensional electrons in InGaAs/InP and GaAs/AlGaAs. Physical Review B, 2012, 86, .	1.1	8
165	Optimization of metamorphic buffers for MBE growth of high quality AlInSb/InSb quantum structures: Suppression of hillock formation. Journal of Crystal Growth, 2017, 477, 7-11.	0.7	8
166	A Tunable Unidirectional Source for GUSTOâ€™s Local Oscillator at 4.74 THz. IEEE Transactions on Terahertz Science and Technology, 2022, 12, 144-150.	2.0	8
167	Magnetoâ€resonant tunneling from a lightly doped contact region interacting with quasiâ€twoâ€dimensional states in an accumulation layer. Journal of Applied Physics, 1990, 68, 4313-4315.	1.1	7
168	Patterning the second-order optical nonlinearity of asymmetric quantum wells by ion implantation enhanced intermixing. Applied Physics Letters, 1998, 72, 3097-3099.	1.5	7
169	High absorption GaAs/AlGaAs quantum well infrared photodetectors. Semiconductor Science and Technology, 2002, 17, L41-L43.	1.0	7
170	Single-photon emission from the natural quantum dots in the InAs/GaAs wetting layer. Physical Review B, 2011, 84, .	1.1	7
171	Three-spin coherent oscillations and interference. Physical Review B, 2015, 91, .	1.1	7
172	Growth and characterization of epitaxial aluminum layers on gallium-arsenide substrates for superconducting quantum bits. Superconductor Science and Technology, 2016, 29, 064004.	1.8	7
173	Thin film metrology and microwave loss characterization of indium and aluminum/indium superconducting planar resonators. Journal of Applied Physics, 2018, 123, .	1.1	7
174	Low-frequency impedance of quantized Hall conductors. Physical Review B, 2000, 62, 12990-12996.	1.1	6
175	Asymmetry in the dark current low frequency noise characteristics of Bâ€“B and Bâ€“C quantum well infrared photodetectors from 10 to 80 K. Journal of Applied Physics, 2000, 87, 2400-2407.	1.1	6
176	Thermal Oxidation of III-V Materials and Heterostructures. Journal of the Electrochemical Society, 2002, 149, G581.	1.3	6
177	Thermopower of a double quantum well in a parallel magnetic field. Physical Review B, 2004, 70, .	1.1	6
178	Pressure tuning of GaInNAs laser diodes in external cavity. , 2005, , .		6
179	Temperature dependence of currentâ€“voltage characteristics of terahertz quantum-well photodetectors. Semiconductor Science and Technology, 2009, 24, 115014.	1.0	6
180	The effect of In-flush on the optical anisotropy of InAs/GaAs quantum dots. Journal of Applied Physics, 2012, 111, 033510.	1.1	6

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